What is claimed is:

1. A substrate treating apparatus comprising:

an inner chamber in which a first space is formed;

a first outer chamber surrounding the inner chamber and forming a second space separated from the first space;

a susceptor disposed in the first space and adapted to support a substrate;

a first exhaust line connected to the inner chamber and exhausting a gas in the first space to the outside;

a process gas supply member adapted to supply a process gas for treating the substrate to the first space; ~~and~~

a monitor module disposed in the second space and adapted to monitor a state of the first space; and

a second exhaust line connected to the first outer chamber and exhausting a gas in the second space to the outside.~~,~~

2. A substrate treating apparatus comprising:

an inner chamber in which a first space is formed;

a first outer chamber surrounding the inner chamber and forming a second space separated from the first space;

a susceptor disposed in the first space and adapted to support a substrate;

a first exhaust line connected to the inner chamber and exhausting a gas in the first space to the outside;

a process gas supply member adapted to supply a process gas for treating the substrate to the first space; and

a monitor module disposed in the second space and adapted to monitor a state of the first space,

~~The substrate treating apparatus of claim 1,~~ wherein the first outer chamber is provided in plurality, the plurality of first outer chambers are disposed to be spaced apart from each other along the circumference of the inner chamber, and each of the first outer chambers forms the second space; and

wherein the monitor module is provided to the respective second spaces.

3. The substrate treating apparatus of claim 1 or 2, wherein the first outer chamber is provided along the circumference of the inner chamber; and

wherein the second space exhibits a shape of ring surrounding the first space.

4. A substrate treating apparatus comprising:

an inner chamber in which a first space is formed;

a first outer chamber surrounding the inner chamber and forming a second space separated from the first space;

a susceptor disposed in the first space and adapted to support a substrate;

a first exhaust line connected to the inner chamber and exhausting a gas in the first space to the outside;

a process gas supply member adapted to supply a process gas for treating the substrate to the first space; and

a monitor module disposed in the second space and adapted to monitor a state of the first space,

~~The substrate treating apparatus of claim 1,~~ wherein the first outer chamber comprises:

an upper plate having one end connected to a sidewall of the inner chamber;

a lower plate disposed below the upper plate and having one end connected to the sidewall of the inner chamber; and

a sidewall facing the sidewall of the inner chamber and connecting the other end of the upper plate to the other end of the lower plate,

wherein the second space is formed by combination of the upper plate, the lower plate, the sidewall of the inner chamber, and the sidewall of the

first outer chamber.

~~5. The substrate treating apparatus of claim 1, further comprising:~~

~~a second exhaust line connected to the first outer chamber and exhausting a gas in the second space to the outside.~~

~~6~~5. A substrate treating apparatus comprising:

an inner chamber in which a first space is formed;

a first outer chamber surrounding the inner chamber and forming a second space separated from the first space;

a susceptor disposed in the first space and adapted to support a substrate;

a first exhaust line connected to the inner chamber and exhausting a gas in the first space to the outside;

a process gas supply member adapted to supply a process gas for treating the substrate to the first space;

a monitor module disposed in the second space and adapted to monitor a state of the first space; and~~The substrate treating apparatus of claim 1, further comprising:~~

a process kit disposed in the second space and adapted to control a substrate treating process.

~~7~~6. A substrate treating apparatus comprising:

an inner chamber in which a first space is formed;

a first outer chamber surrounding the inner chamber and forming a second space separated from the first space;

a susceptor disposed in the first space and adapted to support a substrate;

a first exhaust line connected to the inner chamber and exhausting a gas in the first space to the outside;

a process gas supply member adapted to supply a process gas for treating the substrate to the first space; and

a monitor module disposed in the second space and adapted to monitor a state of the first space,

~~The substrate treating apparatus of claim 1,~~ wherein the monitor module comprises:

a first monitor sensor fixedly mounted on the sidewall of the inner chamber, having a portion exposed to the first space, and adapted to measure a state variation of the first space; and

a second monitor sensor disposed in the second space and adapted to measure a pressure variation of the second space.

~~8~~7. The substrate treating apparatus of claim ~~7~~6, wherein the first monitor sensor measures at least one of a temperature variation, a pressure variation, an intensity ~~magnitude~~ variation of an electric field, and a density variation of a process gas in the first space.

~~9~~8. The substrate treating apparatus of claim ~~7~~6, wherein the process gas supply member comprises:

a process gas supply line disposed in the second space, connected to the sidewall of the inner chamber, and supplying a process gas to the first space.

~~10~~9. The substrate treating apparatus of claim ~~9~~8, wherein the process gas supply member further comprises:

a generator mounted on the process gas supply line and adapted to excite a process gas into a plasma sate.

1~~0~~1. A substrate treating apparatus comprising:

an inner chamber in which a first space is formed;

a first outer chamber surrounding the inner chamber and forming a

second space separated from the first space;

a susceptor disposed in the first space and adapted to support a substrate;

a first exhaust line connected to the inner chamber and exhausting a gas in the first space to the outside;

a process gas supply member adapted to supply a process gas for treating the substrate to the first space;

a monitor module disposed in the second space and adapted to monitor a state of the first space;~~The substrate treating apparatus of claim 1, further comprising:~~

a second outer chamber surrounding the first outer chamber outside the first outer chamber and forming a third space separated from the second space; and

a third exhaust line connected to the second outer chamber and exhausting a gas in the third space to the outside.

1~~2~~1. The substrate treating apparatus of claim 1~~1~~0, further comprising:

an exhaust pump mounted on the first exhaust line; and

a first control valve mounted on the first exhaust line between the inner chamber and the exhaust pump,

wherein the third exhaust line is connected to the first exhaust line in a section between the first control valve and the exhaust pump, and a control valve is mounted on the third exhaust line.

1~~3~~2. The substrate treating apparatus of claim 10~~1~~5, further comprising:

a first exhaust pump mounted on the first exhaust line; and

a second exhaust pump mounted on the second exhaust line.

1~~4~~3. A process treating member comprising:

an inner chamber in which a first space is formed;

a first outer chamber surrounding the inner chamber and forming a second space separated from the first space;

a susceptor disposed in the first space and adapted to support a substrate;

a first exhaust line connected to the inner chamber and exhausting a gas in the first space to the outside; ~~and~~

a monitor module disposed in the second space and adapted to monitor a state of the first space;

a second outer chamber surrounding the first outer chamber outside the first outer chamber and forming a third space separated from the second space; and

a exhaust line connected to the second outer chamber and exhausting a gas in the second space to the outside.

15~~3~~4. A process treating member comprising:

an inner chamber in which a first space is formed;

a first outer chamber surrounding the inner chamber and forming a second space separated from the first space;

a susceptor disposed in the first space and adapted to support a substrate;

a first exhaust line connected to the inner chamber and exhausting a gas in the first space to the outside;~~The process treating member of claim 14, further comprising:~~

a second outer chamber surrounding the first outer chamber outside the first outer chamber and forming a third space separated from the second space; and

a third exhaust line connected to the second outer chamber and exhausting a gas in the third space to the outside.

16~~5~~. A process treating member comprising:

an inner chamber in which a first space is formed;

a first outer chamber surrounding the inner chamber and forming a second space separated from the first space;

a susceptor disposed in the first space and adapted to support a substrate;

a first exhaust line connected to the inner chamber and exhausting a gas in the first space to the outside; and

a monitor module disposed in the second space and adapted to monitor a state of the first space,

~~The process treating member of claim 14,~~ wherein the monitor module comprises:

a first monitor sensor fixedly mounted on the sidewall of the inner chamber, having a portion exposed to the first space, and adapted to measure a state variation of the first space; and

a second monitor sensor disposed in the second space and adapted to measure a pressure variation of the second space.

17~~6~~. The process treating member of claim 16~~5~~, further comprising:

a process kit disposed in the second space and adapted to control a substrate treating process.

187. The process treating member of claim 165, wherein the second space exhibits a shape of ring surrounding the first space; and

wherein the monitor module is provided in plurality, and the plurality of monitor modules are disposed to be spaced apart from each other along the second space.

198. The process treating member of claim 165, wherein the first outer chamber is disposed to be spaced apart from each other along the circumference of the inner chamber and forms the second space; and

wherein the monitor module is provided to the respective second spaces.

~~20~~19. The process treating member of claim 1~~6~~5, further comprising:

a second exhaust line connected to the first outer chamber and exhausting a gas in the second space to the outside.

2~~1~~0. A substrate treating method comprising:

providing a process gas supplied to a first space in an inner chamber to treat a substrate; and

monitoring a state of the first space by a monitor module surrounding the inner chamber and disposed inside a first outer chamber forming a second space separated from the first space;

wherein a gas in the first space is exhausted to the outside through an exhaust line connected to the inner chamber; and

wherein the second space is maintained at a higher pressure than the first space.

~~22. The substrate treating method of claim 21, wherein a gas in the first space is exhausted to the outside through an exhaust line connected to the inner chamber; and~~

~~wherein the second space is maintained at a higher pressure than the first space.~~

2~~3~~1. A substrate treating method comprising:

providing a process gas supplied to a first space in an inner chamber to treat a substrate; and

monitoring a state of the first space by a monitor module surrounding the inner chamber and disposed inside a first outer chamber forming a second space separated from the first space,

~~The substrate treating method of claim 21,~~ wherein the first space and the second space are maintained at a pressure lower than an atmospheric pressure.

2~~1~~2. The substrate treating method of claim 2~~1~~0 or 21~~3~~, wherein the monitor module measures at least one of a temperature variation, a pressure variation, a magnitude variation of an electric field, and a density variation of a process gas in the first space.

253. The substrate treating method of claim 242, wherein a second outer chamber is provided outside the first outer chamber to surround the first outer chamber and forms a third space separated from the second space; and

wherein the third space is maintained in a vacuum state while a substrate treatment is performed.